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## Trench gate field-stop IGBT, M series 650 V, 10 A low-loss in TO-220 package

Datasheet - production data

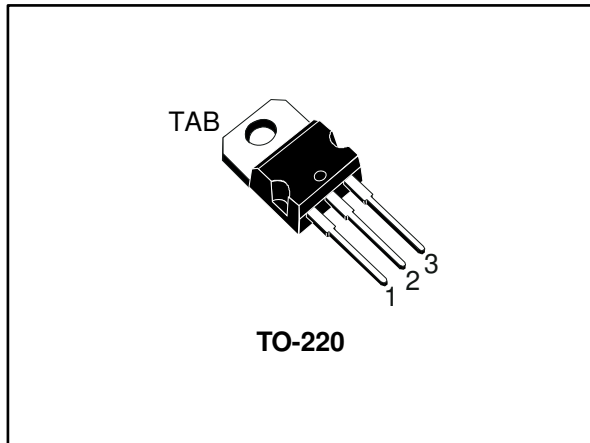
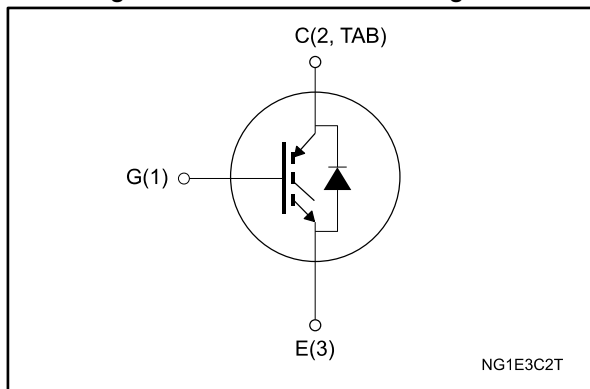


Figure 1: Internal schematic diagram



### Features

- 6  $\mu$ s of short-circuit withstand time
- $V_{CE(sat)} = 1.55$  V (typ.) @  $I_c = 10$  A
- Tight parameter distribution
- Safer paralleling
- Positive  $V_{CE(sat)}$  temperature coefficient
- Low thermal resistance
- Soft and very fast recovery antiparallel diode
- Maximum junction temperature:  $T_J = 175$  °C

### Applications

- Motor control
- UPS
- PFC
- General purpose inverter

### Description

This device is an IGBT developed using an advanced proprietary trench gate field-stop structure. The device is part of the M series IGBTs, which represent an optimal balance between inverter system performance and efficiency where low-loss and short-circuit functionality are essential. Furthermore, the positive  $V_{CE(sat)}$  temperature coefficient and tight parameter distribution result in safer paralleling operation.

Table 1: Device summary

Order code	Marking	Package	Packing
STGP10M65DF2	G10M65DF2	TO-220	Tube

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## Contents

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# 1 Electrical ratings

**Table 2: Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{CES}$	Collector-emitter voltage ( $V_{GE} = 0$ V)	650	V
$I_C$	Continuous collector current at $T_C = 25$ °C	20	A
	Continuous collector current at $T_C = 100$ °C	10	
$I_{CP}^{(1)}$	Pulsed collector current	40	A
$V_{GE}$	Gate-emitter voltage	±20	V
$I_F$	Continuous forward current at $T_C = 25$ °C	20	A
	Continuous forward current at $T_C = 100$ °C	10	
$I_{FP}^{(1)}$	Pulsed forward current	40	A
$P_{TOT}$	Total dissipation at $T_C = 25$ °C	115	W
$T_{STG}$	Storage temperature range	- 55 to 150	°C
$T_J$	Operating junction temperature range	- 55 to 175	

**Notes:**

<sup>(1)</sup>Pulse width limited by maximum junction temperature.

**Table 3: Thermal data**

Symbol	Parameter	Value	Unit
$R_{thJC}$	Thermal resistance junction-case IGBT	1.3	°C/W
$R_{thJC}$	Thermal resistance junction-case diode	2.08	
$R_{thJA}$	Thermal resistance junction-ambient	62.5	

## 2 Electrical characteristics

$T_C = 25\text{ °C}$  unless otherwise specified

**Table 4: Static characteristics**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)CES}$	Collector-emitter breakdown voltage	$V_{GE} = 0\text{ V}$ , $I_C = 250\text{ }\mu\text{A}$	650			V
$V_{CE(sat)}$	Collector-emitter saturation voltage	$V_{GE} = 15\text{ V}$ , $I_C = 10\text{ A}$		1.55	2.0	V
		$V_{GE} = 15\text{ V}$ , $I_C = 10\text{ A}$ , $T_J = 125\text{ °C}$		1.9		
		$V_{GE} = 15\text{ V}$ , $I_C = 10\text{ A}$ , $T_J = 175\text{ °C}$		2.1		
$V_F$	Forward on-voltage	$I_F = 10\text{ A}$		1.5	2.25	V
		$I_F = 10\text{ A}$ , $T_J = 125\text{ °C}$		1.3		
		$I_F = 10\text{ A}$ , $T_J = 175\text{ °C}$		1.2		
$V_{GE(th)}$	Gate threshold voltage	$V_{CE} = V_{GE}$ , $I_C = 250\text{ }\mu\text{A}$	5	6	7	V
$I_{CES}$	Collector cut-off current	$V_{GE} = 0\text{ V}$ , $V_{CE} = 650\text{ V}$			25	$\mu\text{A}$
$I_{GES}$	Gate-emitter leakage current	$V_{CE} = 0\text{ V}$ , $V_{GE} = \pm 20\text{ V}$			$\pm 250$	$\mu\text{A}$

**Table 5: Dynamic characteristics**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{ies}$	Input capacitance	$V_{CE} = 25\text{ V}$ , $f = 1\text{ MHz}$ , $V_{GE} = 0\text{ V}$	-	840	-	pF
$C_{oes}$	Output capacitance		-	63	-	
$C_{res}$	Reverse transfer capacitance		-	16	-	
$Q_g$	Total gate charge	$V_{CC} = 520\text{ V}$ , $I_C = 10\text{ A}$ , $V_{GE} = 0\text{ to }15\text{ V}$ (see <a href="#">Figure 30: "Gate charge test circuit"</a> )	-	28	-	nC
$Q_{ge}$	Gate-emitter charge		-	6	-	
$Q_{gc}$	Gate-collector charge		-	12	-	



Table 6: IGBT switching characteristics (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{CE} = 400\text{ V}$ , $I_C = 10\text{ A}$ , $V_{GE} = 15\text{ V}$ , $R_G = 22\ \Omega$ (see <a href="#">Figure 29: "Test circuit for inductive load switching"</a> )		19	-	ns
$t_r$	Current rise time			7.4	-	ns
$(di/dt)_{on}$	Turn-on current slope			1086	-	A/ $\mu$ s
$t_{d(off)}$	Turn-off-delay time			91	-	ns
$t_f$	Current fall time			92	-	ns
$E_{on}^{(1)}$	Turn-on switching energy			0.12	-	mJ
$E_{off}^{(2)}$	Turn-off switching energy			0.27	-	mJ
$E_{ts}$	Total switching energy			0.39	-	mJ
$t_{d(on)}$	Turn-on delay time	$V_{CE} = 400\text{ V}$ , $I_C = 10\text{ A}$ , $V_{GE} = 15\text{ V}$ , $R_G = 22\ \Omega$ , $T_J = 175\text{ }^\circ\text{C}$ (see <a href="#">Figure 29: "Test circuit for inductive load switching"</a> )		18	-	ns
$t_r$	Current rise time			9	-	ns
$(di/dt)_{on}$	Turn-on current slope			890	-	A/ $\mu$ s
$t_{d(off)}$	Turn-off-delay time			90	-	ns
$t_f$	Current fall time			170	-	ns
$E_{on}^{(1)}$	Turn-on switching energy			0.26	-	mJ
$E_{off}^{(2)}$	Turn-off switching energy			0.4	-	mJ
$E_{ts}$	Total switching energy			0.66	-	mJ
$t_{sc}$	Short-circuit withstand time	$V_{CC} \leq 400\text{ V}$ , $V_{GE} = 13\text{ V}$ , $T_{Jstart} = 150\text{ }^\circ\text{C}$	10		-	$\mu$ s
		$V_{CC} \leq 400\text{ V}$ , $V_{GE} = 15\text{ V}$ , $T_{Jstart} = 150\text{ }^\circ\text{C}$	6		-	$\mu$ s

**Notes:**

(1)Including the reverse recovery of the diode.

(2)Including the tail of the collector current.

Table 7: Diode switching characteristics (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{rr}$	Reverse recovery time	$I_F = 10\text{ A}$ , $V_R = 400\text{ V}$ , $V_{GE} = 15\text{ V}$ , $di/dt = 1000\text{ A}/\mu\text{s}$ (see <a href="#">Figure 29: "Test circuit for inductive load switching"</a> )	-	96	-	ns
$Q_{rr}$	Reverse recovery charge		-	373	-	nC
$I_{rrm}$	Reverse recovery current		-	13	-	A
$dl_{rr}/dt$	Peak rate of fall of reverse recovery current during $t_b$		-	661	-	A/ $\mu$ s
$E_{rr}$	Reverse recovery energy		-	52	-	$\mu$ J
$t_{rr}$	Reverse recovery time	$I_F = 10\text{ A}$ , $V_R = 400\text{ V}$ , $V_{GE} = 15\text{ V}$ , $di/dt = 1000\text{ A}/\mu\text{s}$ , $T_J = 175\text{ }^\circ\text{C}$ (see <a href="#">Figure 29: "Test circuit for inductive load switching"</a> )	-	201	-	ns
$Q_{rr}$	Reverse recovery charge		-	1352	-	nC
$I_{rrm}$	Reverse recovery current		-	19	-	A
$dl_{rr}/dt$	Peak rate of fall of reverse recovery current during $t_b$		-	405	-	A/ $\mu$ s
$E_{rr}$	Reverse recovery energy		-	150	-	$\mu$ J

## 2.1 Electrical characteristics (curves)

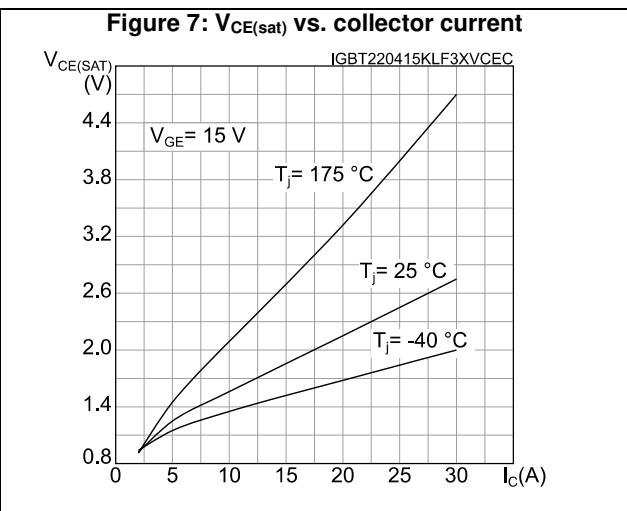
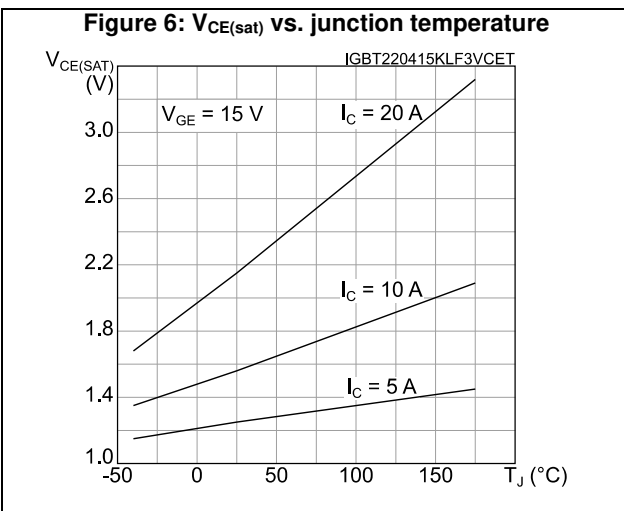
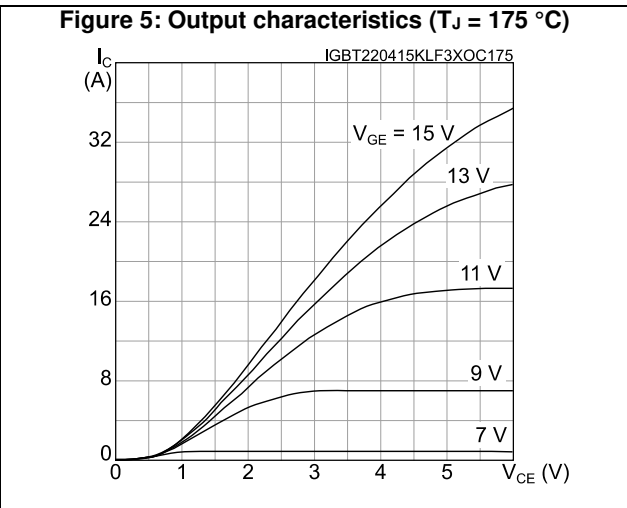
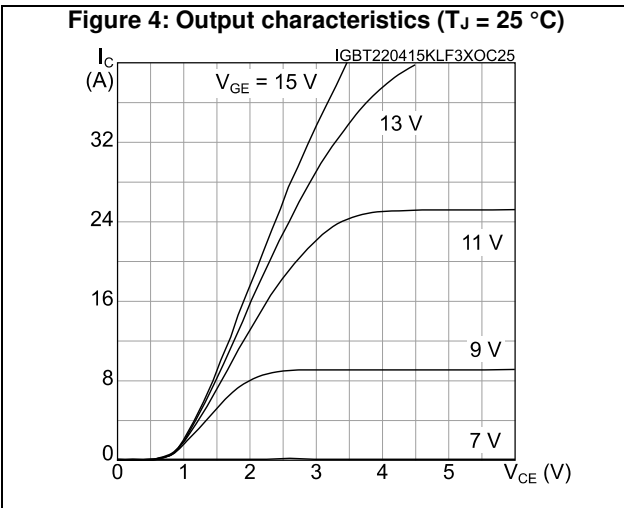
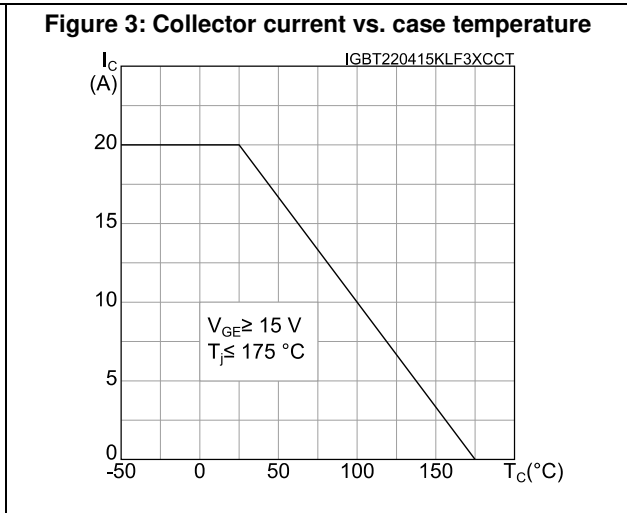
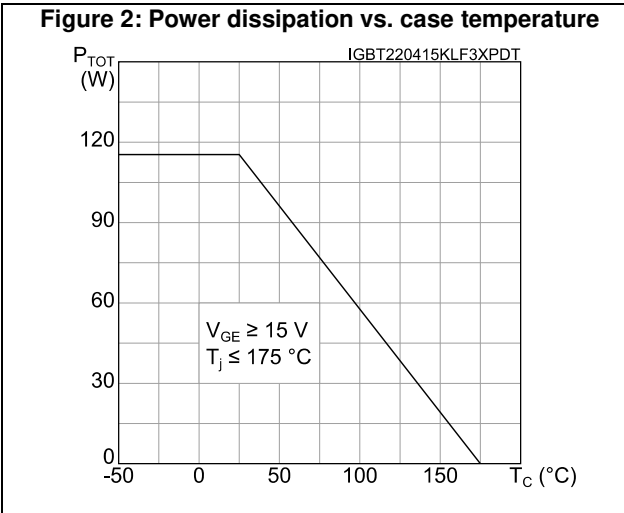


Figure 8: Collector current vs. switching frequency

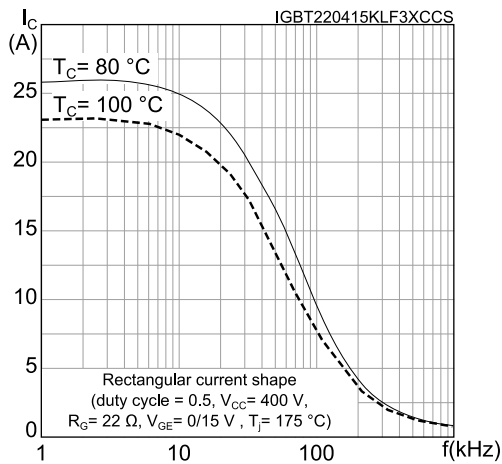


Figure 9: Forward bias safe operating area

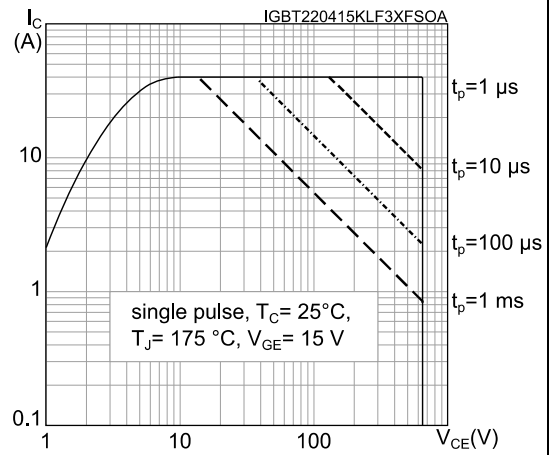


Figure 10: Transfer characteristics

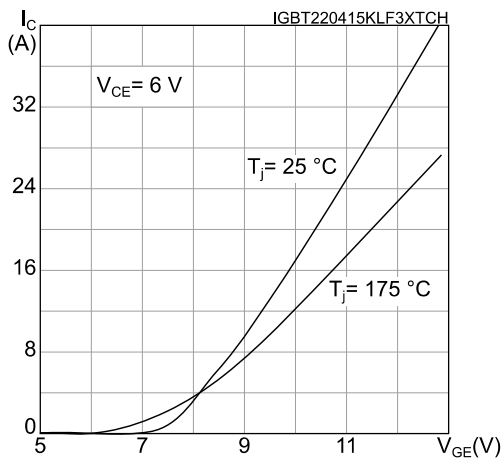


Figure 11: Diode V\_F vs. forward current

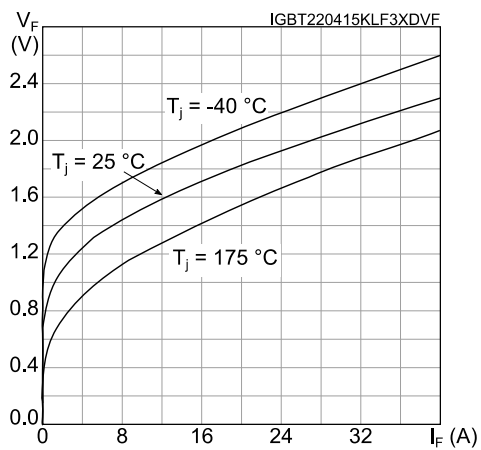


Figure 12: Normalized V\_GE(th) vs. junction temperature

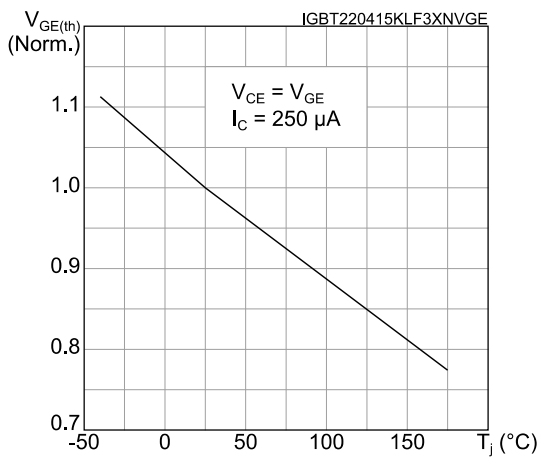
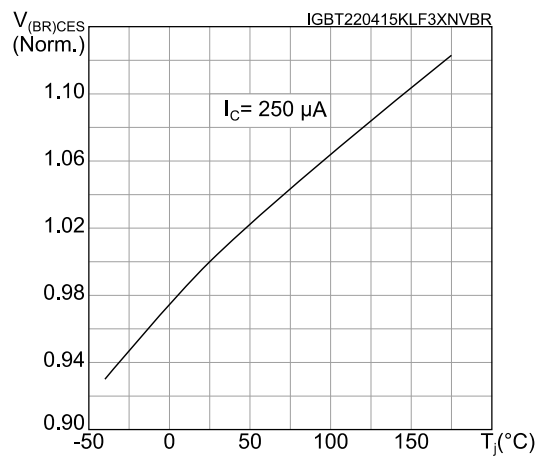
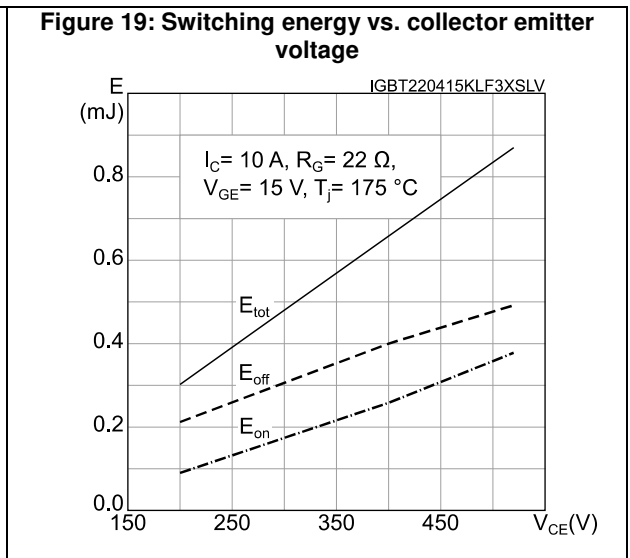
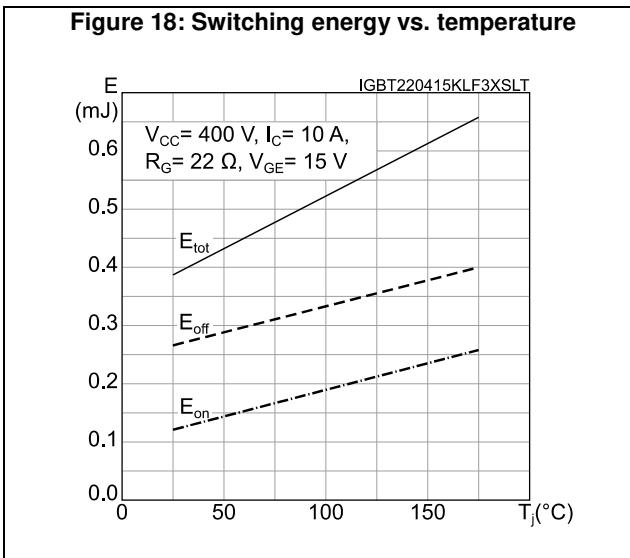
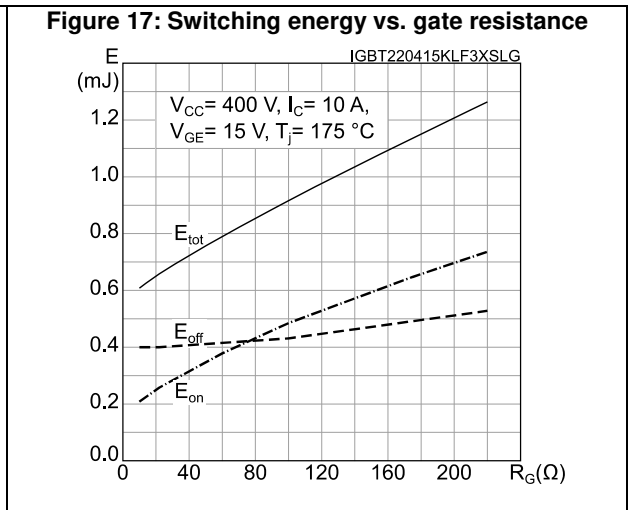
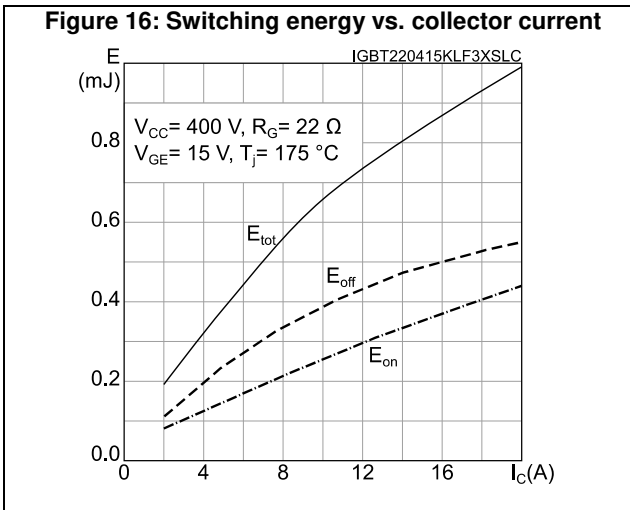
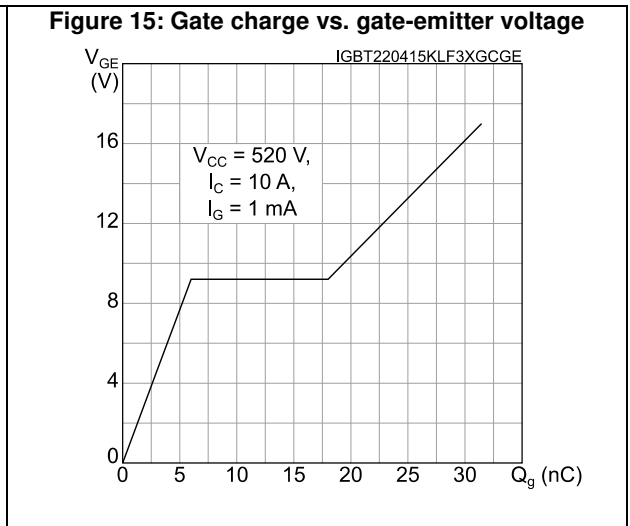
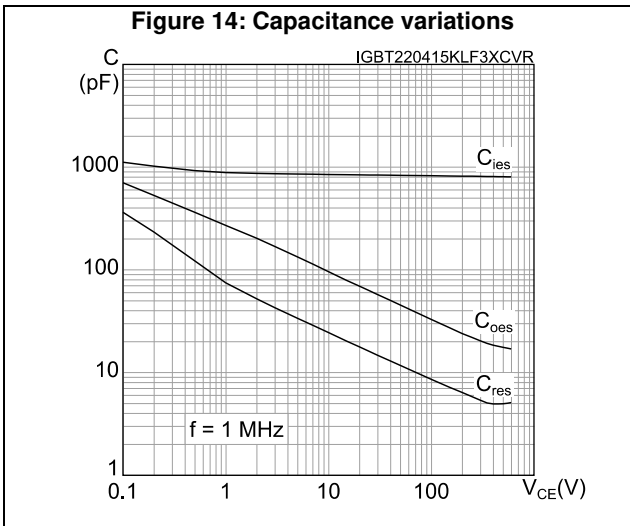


Figure 13: Normalized V\_(BR)CES vs. junction temperature







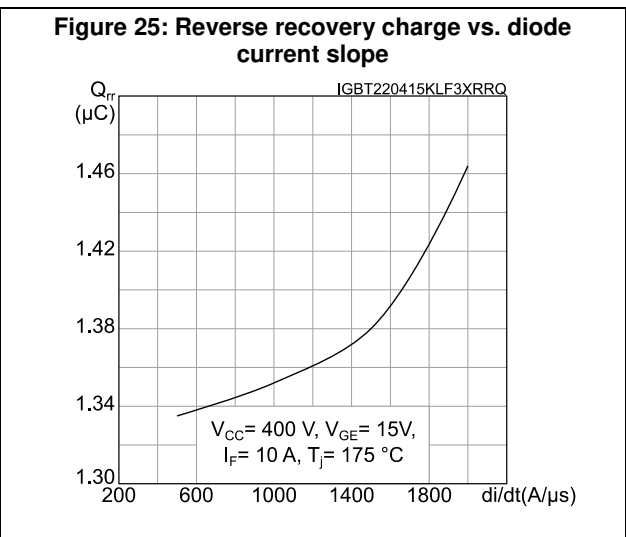
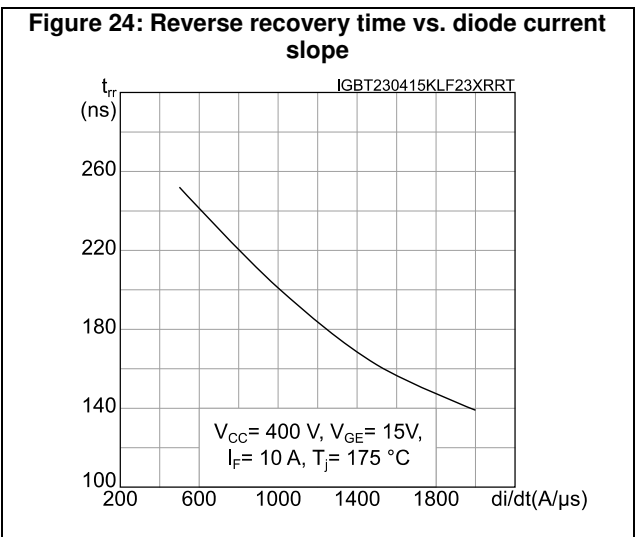
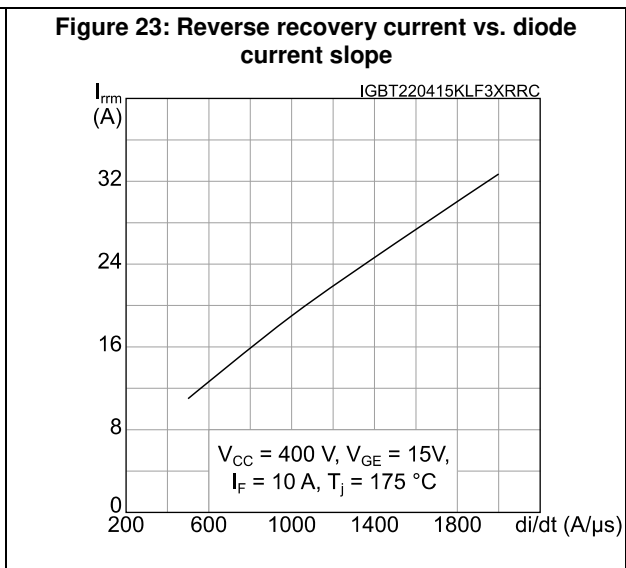
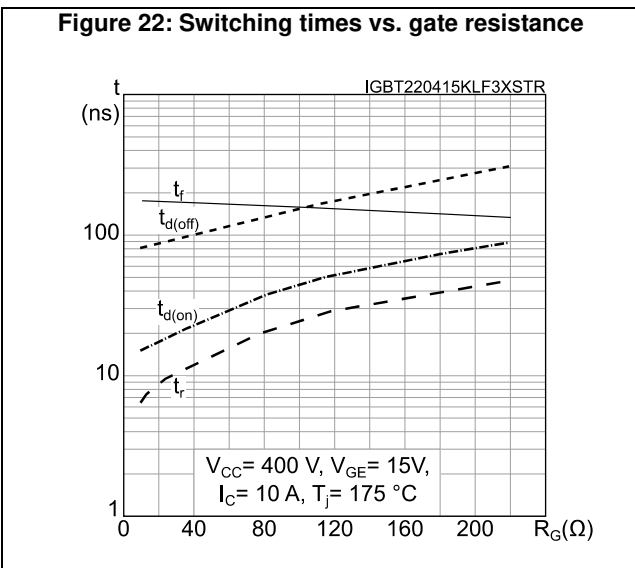
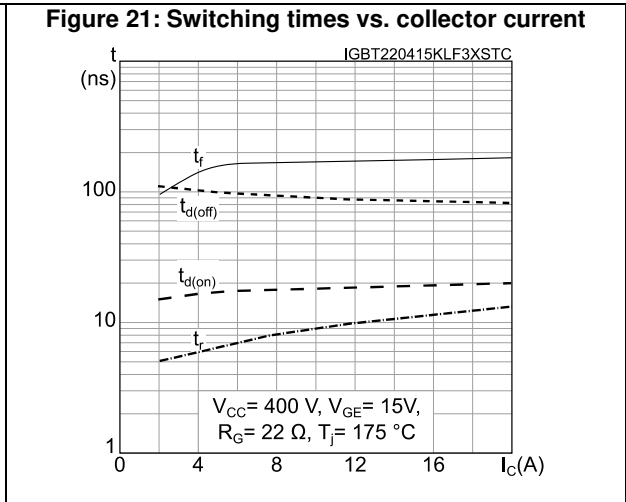
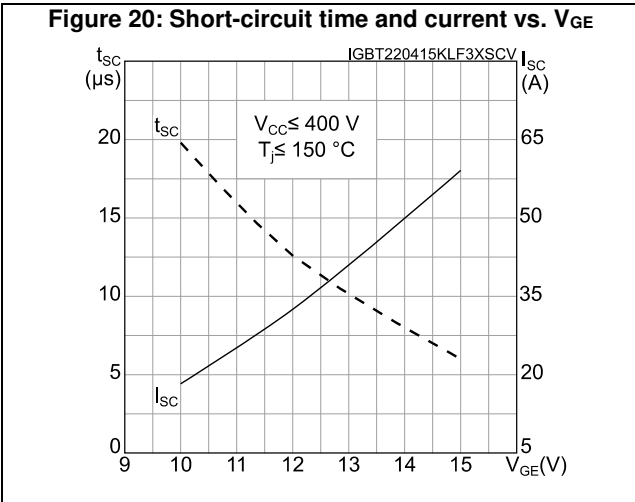


Figure 26: Reverse recovery energy vs. diode current slope

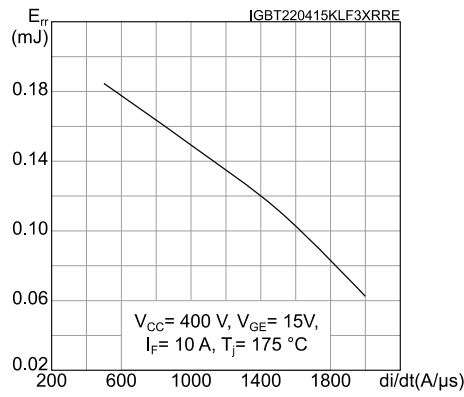


Figure 27: Thermal impedance for IGBT

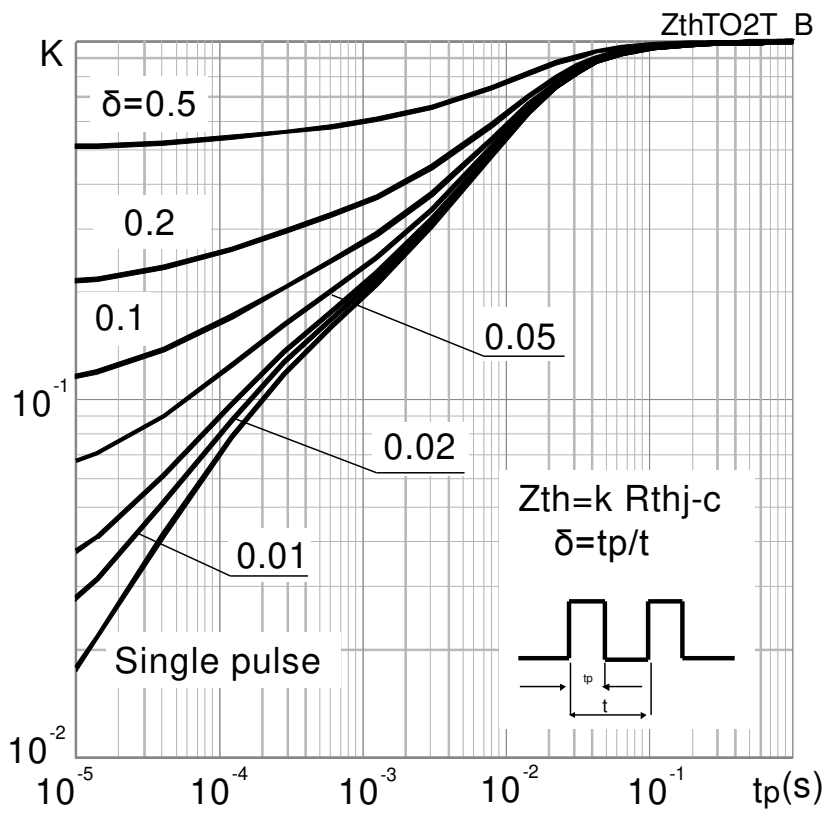
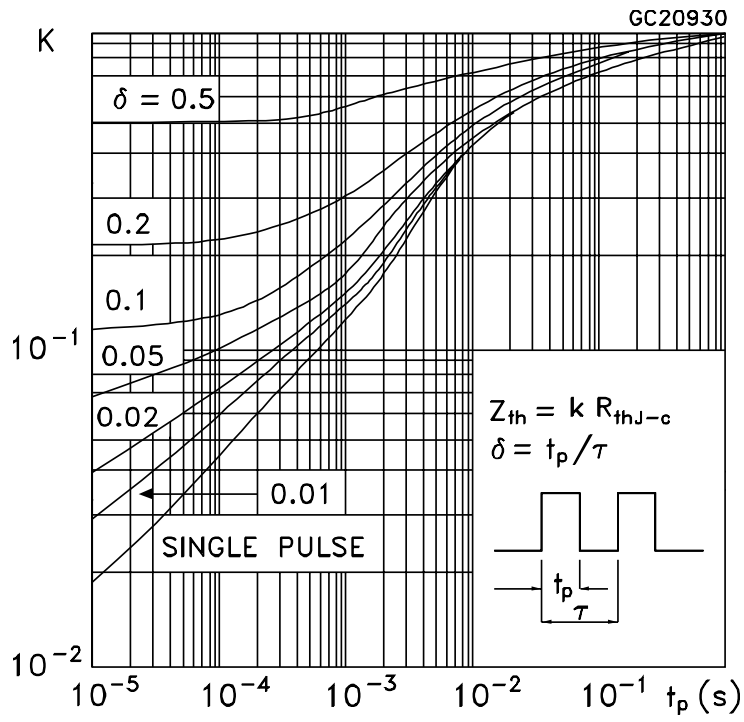
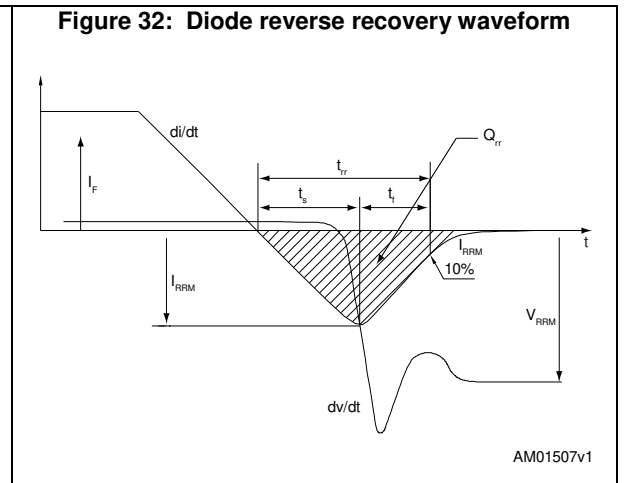
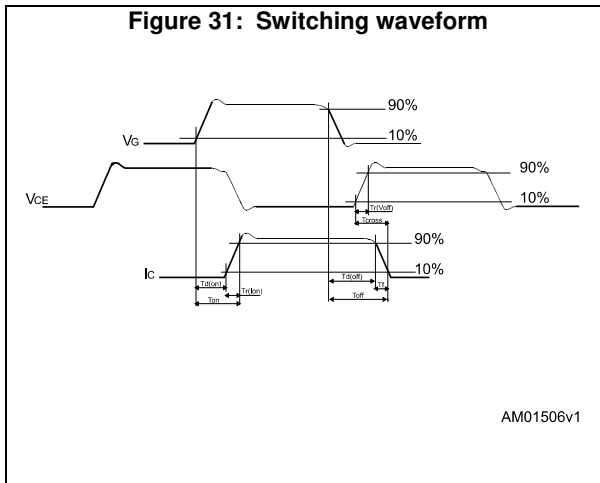
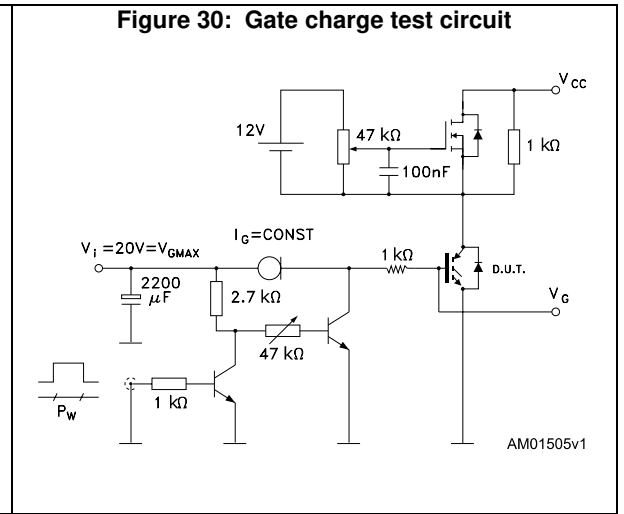
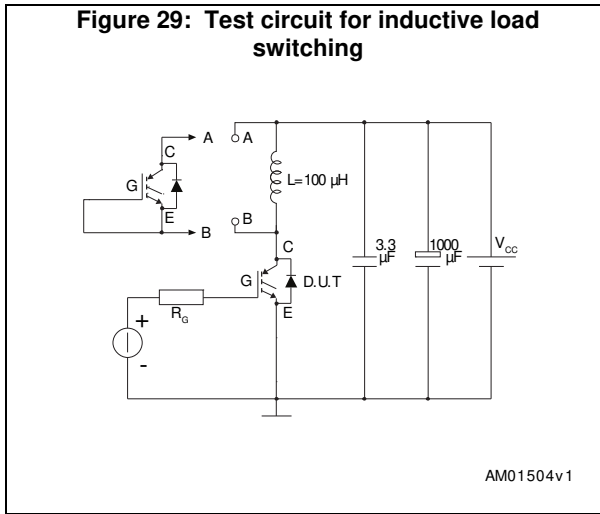


Figure 28: Thermal impedance for diode



### 3 Test circuits



## 4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK® is an ST trademark.



### 4.1 TO-220 type A package information

Figure 33: TO-220 type A package outline

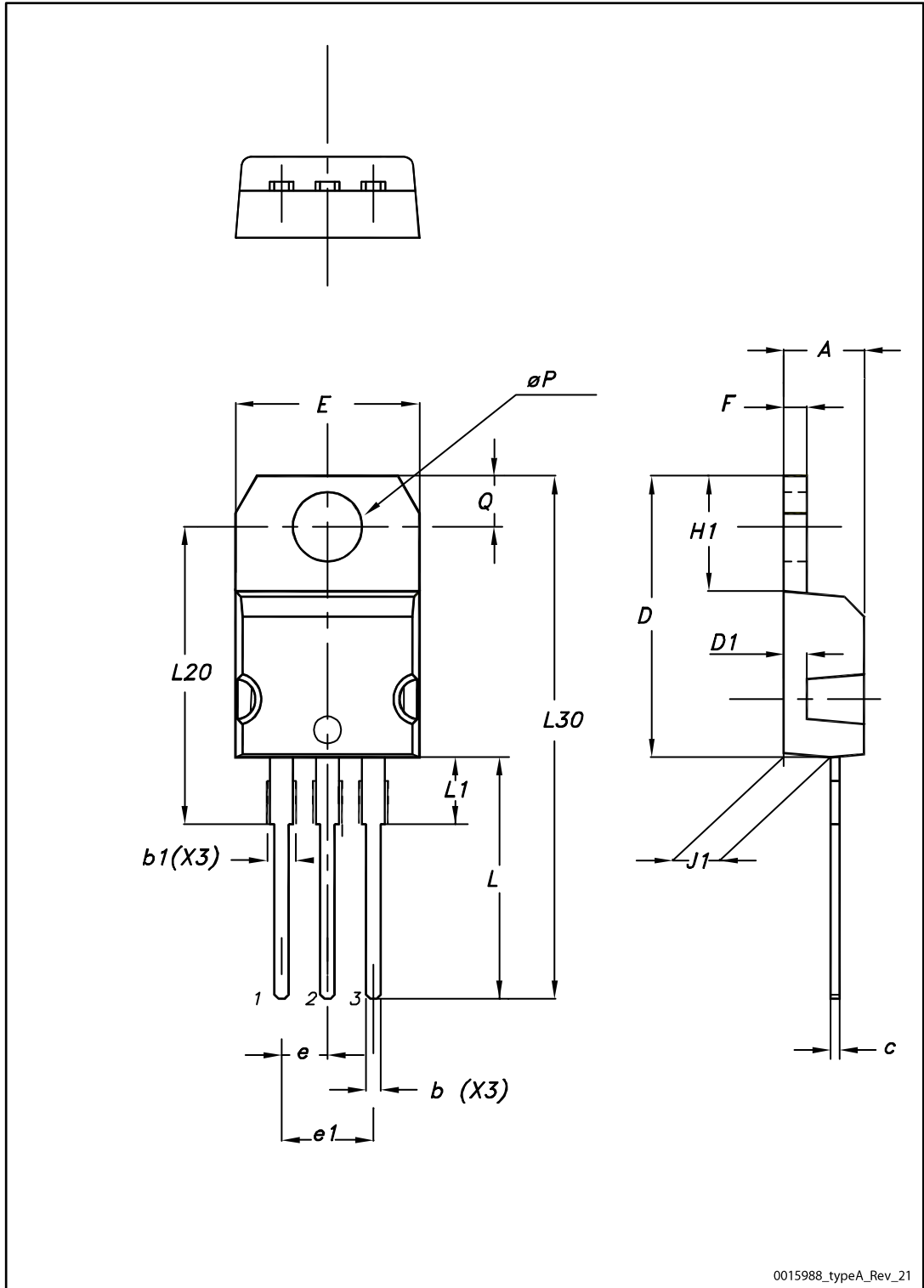


Table 8: TO-220 type A mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.55
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10.00		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13.00		14.00
L1	3.50		3.93
L20		16.40	
L30		28.90	
øP	3.75		3.85
Q	2.65		2.95

## 5 Revision history

**Table 9: Document revision history**

Date	Revision	Changes
10-Feb-2015	1	First release.
23-Apr-2015	2	Minor text edits throughout document Document status promoted to 'Production data' In Section 2 Electrical characteristics: - updated Table 4: Static characteristics - updated Table 5: Dynamic characteristics - updated Table 6: IGBT switching characteristics (inductive load) - updated Table 7: Diode switching characteristics (inductive load) Added Section 2.1 Electrical characteristics (curves)
31-Jul-2015	3	Updated Table 7: Diode switching characteristics (inductive load)
19-Oct-2015	4	Updated <i>Table 5: "Dynamic characteristics"</i> and <i>Table 6: "IGBT switching characteristics (inductive load)"</i> . Updated <i>Figure 8: "Collector current vs. switching frequency"</i> .
07-Apr-2017	5	Modified title, features and applications on cover page Modified <i>Table 4: "Static characteristics"</i> , <i>Table 6: "IGBT switching characteristics (inductive load)"</i> and <i>Table 7: "Diode switching characteristics (inductive load)"</i> Minor text changes.

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